## 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 3 A
- Reverse voltage: V<sub>R</sub> ≤ 60 V
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature T<sub>i</sub> ≤ 175 °C

## 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption application

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 165 °C; square wave	-	-	3	Α
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C	-	-	60	V
V <sub>F</sub>	forward voltage	$I_F$ = 3 A; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C; pulsed	-	420	475	mV
I <sub>R</sub>	reverse current	$T_j$ = 25 °C; $V_R$ = 60 V; pulsed	-	115	400	μA





High-temperature 60 V, 3 A Schottky barrier rectifier

## 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	4	1 <del>[[-]</del> 2
2	A	anode	SOD128	sym001

<sup>[1]</sup> The marking bar indicates the cathode.

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG6030EVP	SOD128	plastic surface-mounted package; 2 leads	SOD128			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG6030EVP	DB

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	60	V
I <sub>F</sub>	forward current	T <sub>sp</sub> = 160 °C		-	4.2	Α
I <sub>F(AV)</sub>	average forward current	$\bar{\delta}$ = 0.5 ; f = 20 kHz; $T_{amb} \le 95$ °C; square wave	[1]	-	3	А
		$\bar{\delta}$ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 165 °C; square wave		-	3	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	70	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	750	mW
			[3]	-	1250	mW
			[1]	-	2500	mW
T <sub>j</sub>	junction temperature			-	175	°C

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#### High-temperature 60 V, 3 A Schottky barrier rectifier

Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>amb</sub>	ambient temperature		-55	175	°C
T <sub>stg</sub>	storage temperature		-65	175	°C

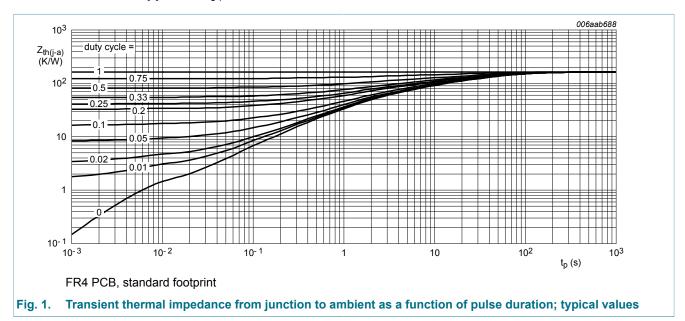
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 9. Thermal characteristics

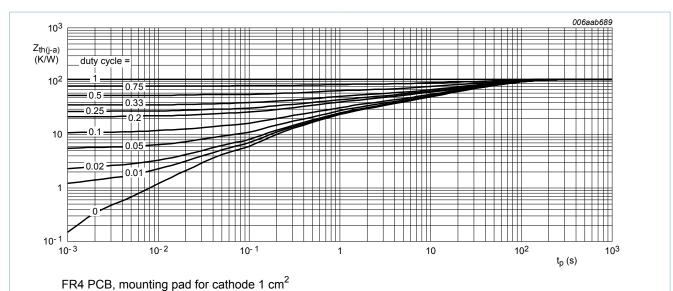
Table 6. Thermal characteristics

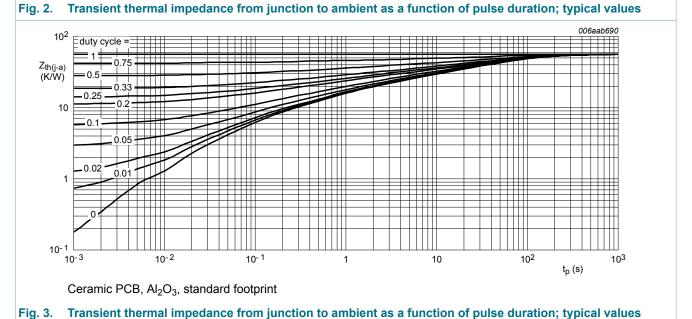
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance	om junction to	[1][2]	-	-	200	K/W
	from junction to		[1][3]	-	-	120	K/W
	ambient		[1][4]	-	-	60	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[5]</u>	-	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.



### High-temperature 60 V, 3 A Schottky barrier rectifier





## 10. Characteristics

Table 7. Characteristics

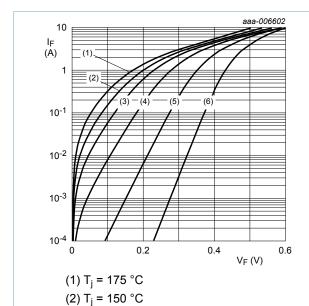
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	$I_F$ = 0.1 A; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C; pulsed	-	275	310	mV
		$I_F$ = 0.5 A; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C; pulsed	-	325	-	mV
		$I_F$ = 1 A; $t_p \le 300 \text{ μs}$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C; pulsed	-	355	400	mV

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## High-temperature 60 V, 3 A Schottky barrier rectifier

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_F$ = 1.5 A; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C; pulsed	-	375	-	mV
		$I_F$ = 2 A; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C; pulsed	-	390	440	mV
		$I_F$ = 3 A; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C; pulsed	-	420	475	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 5 V; T <sub>j</sub> = 25 °C; pulsed	-	7	20	μΑ
		V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C; pulsed	-	9	40	μΑ
		V <sub>R</sub> = 30 V; T <sub>j</sub> = 25 °C; pulsed	-	20	80	μΑ
		V <sub>R</sub> = 60 V; T <sub>j</sub> = 25 °C; pulsed	-	115	400	μΑ
		V <sub>R</sub> = 10 V; T <sub>j</sub> = 125 °C; pulsed	-	9	-	mA
		V <sub>R</sub> = 60 V; T <sub>j</sub> = 125 °C; pulsed	-	70	300	mA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	575	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	200	-	pF
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}$ ; $I_R = 0.5 \text{ A}$ ; $I_{R(meas)} = 0.1 \text{ A}$ ; $I_j = 25  ^{\circ}\text{C}$	-	20	-	ns
$V_{FRM}$	peak forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 40 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	385	-	mV

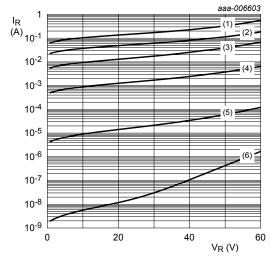


(4)  $T_i = 85 \, ^{\circ}C$ (5)  $T_i = 25$  °C

(3)  $T_i = 125 \, ^{\circ}C$ 

(6)  $T_i = -40 \, ^{\circ}C$ 

Forward current as a function of forward Fig. 4. voltage; typical values



(1)  $T_i = 175 \,^{\circ}C$ 

(2)  $T_j = 150 \, ^{\circ}\text{C}$ 

(3)  $T_i = 125 \, ^{\circ}C$ 

(4)  $T_i = 85 \, ^{\circ}C$ 

(5)  $T_i = 25$  °C

(6)  $T_j = -40 \, ^{\circ}C$ 

Reverse current as a function of reverse Fig. 5. voltage; typical values

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#### High-temperature 60 V, 3 A Schottky barrier rectifier

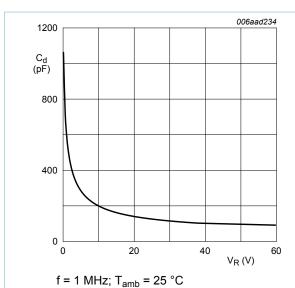
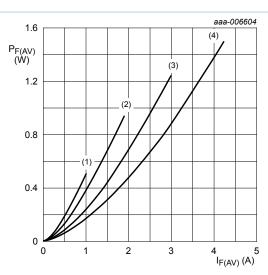


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



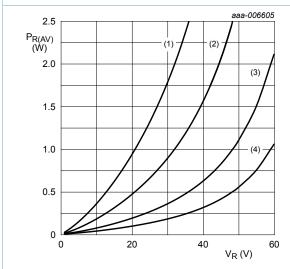
 $T_j = 175 \,^{\circ}\text{C}$ (1)  $\delta = 0.1$ 

 $(2) \delta = 0.2$ 

 $(3) \delta = 0.5$ 

 $(4) \delta = 1$ 

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



T<sub>i</sub> = 150 °C

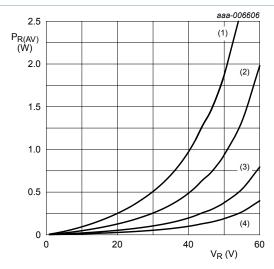
 $(1) \delta = 1$ 

(2)  $\delta = 0.5$ 

(3)  $\delta = 0.2$ 

 $(4) \delta = 0.1$ 

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



T<sub>i</sub> = 125 °C

 $(1) \delta = 1$ 

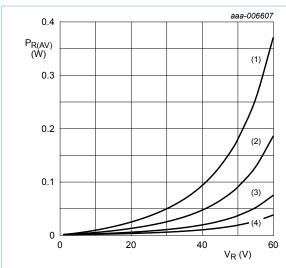
 $(2) \delta = 0.5$ 

 $(3) \delta = 0.2$ 

 $(4) \delta = 0.1$ 

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values

#### High-temperature 60 V, 3 A Schottky barrier rectifier



 $T_i = 85 °C$ 

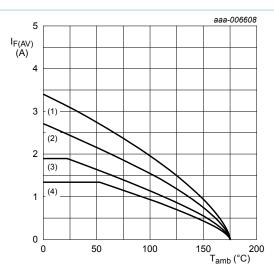
 $(1) \delta = 1$ 

 $(2) \delta = 0.5$ 

 $(3) \delta = 0.2$ 

 $(4) \delta = 0.1$ 

Fig. 10. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T<sub>i</sub> = 175 °C

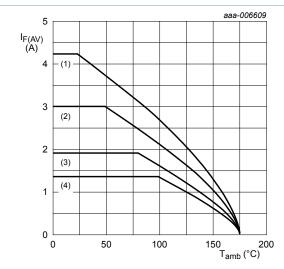
(1)  $\delta = 1$  (DC)

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

T<sub>i</sub> = 175 °C

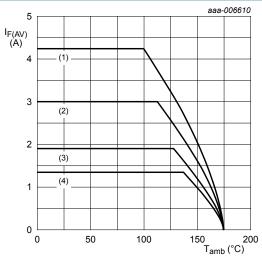
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

 $T_i = 175 \,{}^{\circ}\text{C}$ 

 $(1) \delta = 1 (DC)$ 

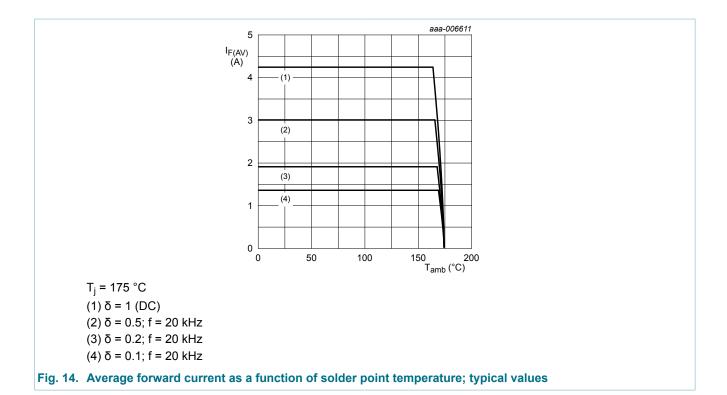
(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

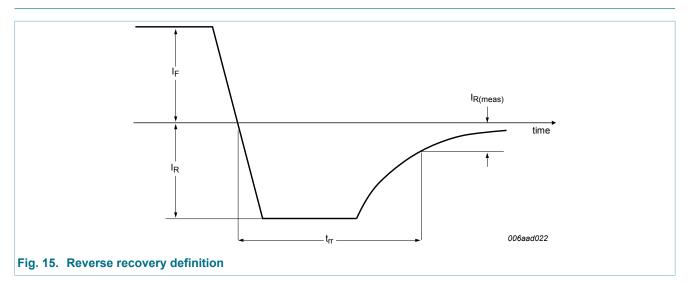
(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 13. Average forward current as a function of ambient temperature; typical values

High-temperature 60 V, 3 A Schottky barrier rectifier

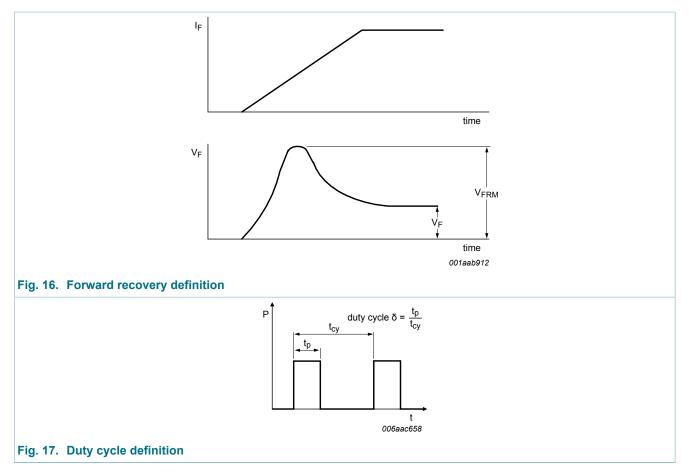


## 11. Test information



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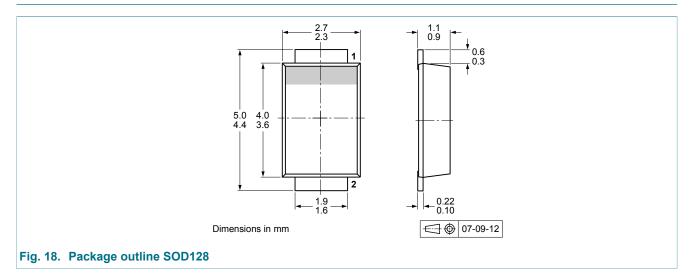
The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 11.1 Quality information

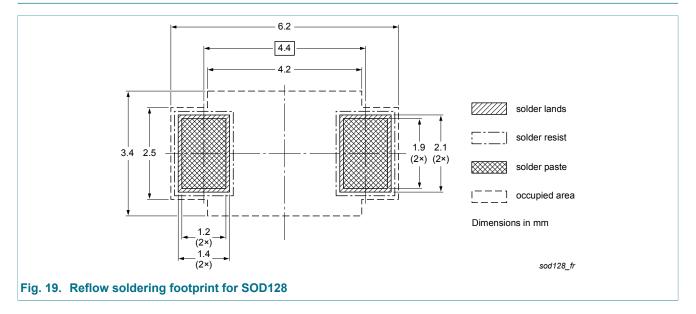
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

High-temperature 60 V, 3 A Schottky barrier rectifier

## 12. Package outline



## 13. Soldering



## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6030EVP v.1	20130304	Product data sheet	-	-

#### High-temperature 60 V, 3 A Schottky barrier rectifier

## 15. Legal information

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